WESTCODE

An IXYS Company

Date:- 17 Mar, 2004

Data Sheet Issue:- 2

Phase Control Thyristor

Types N2086NS060 to N2086NS100

Old Type No.: N610SH06-10

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V_{DRM}	Repetitive peak off-state voltage, (note 1)	600-1000	V
V_{DSM}	Non-repetitive peak off-state voltage, (note 1)	600-1000	V
V_{RRM}	Repetitive peak reverse voltage, (note 1)	600-1000	V
V_{RSM}	Non-repetitive peak reverse voltage, (note 1)	700-1100	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
$I_{T(AV)M}$	Maximum average on-state current. T_{sink}=55°C, (note 2)	2086	A
$I_{T(AV)M}$	Maximum average on-state current. T_{sink}=85°C, (note 2)	1378	A
$I_{T(AV)M}$	Maximum average on-state current. T_{sink}=85°C, (note 3)	792	A
$I_{T(RMS)}$	Nominal RMS on-state current. T_{sink}=25°C, (note 2)	4207	A
$I_{T(d.c.)}$	D.C. on-state current. T_{sink}=25°C, (note 4)	3439	A
I_{TSM}	Peak non-repetitive surge t_p=10ms, V_{rm}=60%V_{RRM}, (note 5)	35.0	kA
I_{TSM2}	Peak non-repetitive surge t_p=10ms, $V_{rm}≤$10V, (note 5)	38.0	kA
I^2t	I^2t capacity for fusing t_p=10ms, V_{rm}=60%V_{RRM}, (note 5)	6.13×10^6	A^2s
I^2t	I^2t capacity for fusing t_p=10ms, $V_{rm}≤$10V, (note 5)	7.22×10^6	A^2s
$(di/dt)_{cr}$	Maximum rate of rise of on-state current (continuous, 50Hz), (Note 6)	250	A/µs
	Maximum rate of rise of on-state current (repetitive, 50Hz, 60s), (Note 6)	500	
	Maximum rate of rise of on-state current (non-repetitive), (Note 6)	1000	
V_{RGM}	Peak reverse gate voltage	5	V
$P_{G(AV)}$	Mean forward gate power	4	W
P_{GM}	Peak forward gate power	30	W
$T_{j\ op}$	Operating temperature range	-40 to +125	°C
T_{stg}	Storage temperature range	-40 to +150	°C

Notes: -
1) De-rating factor of 0.13% per °C is applicable for T_j below 25°C.
2) Double side cooled, single phase; 50Hz, 180° half-sinewave.
3) Single side cooled, single phase; 50Hz, 180° half-sinewave.
4) Double side cooled.
5) Half-sinewave, 125°C T_j initial.
6) V_D=67% V_{DRM}, I_{TM}=1000A, I_{FG}=2A, $t_r≤$0.5µs, T_{case}=125°C.
7) Rated V_{DRM}.

Characteristics

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
V_{TM}	Maximum peak on-state voltage	-	-	1.12	I_{TM}=2550A	V
		-	-	1.49	I_{TM}=6250A	
V_0	Threshold voltage	-	-	0.84		V
r_S	Slope resistance	-	-	0.108		mΩ
dv/dt	Critical rate of rise of off-state voltage	1000	-	-	V_D=80%V_{DRM}, linear ramp, Gate o/c	V/µs
I_{DRM}	Peak off-state current	-	-	100	Rated V_{DRM}	mA
I_{RRM}	Peak reverse current	-	-	100	Rated V_{RRM}	mA
V_{GT}	Gate trigger voltage	-	-	3.0	T_j=25°C, V_D=10V, I_T=3A	V
I_{GT}	Gate trigger current	-	-	300		mA
V_{GD}	Gate non-trigger voltage	-	-	0.25	Rated V_{DRM}	V
I_H	Holding current	-	-	1000	T_j=25°C	mA
t_{gd}	Gate controlled turn-on delay time	-	0.8	1.5	V_D=67%V_{DRM}, I_{TM}=2000A, di/dt=10A/µs, I_{FG}=2A, t_r=0.5µs, T_j=25°C	µs
t_{gt}	Turn-on time	-	1.5	3.0		
Q_{rr}	Recovered Charge	-	1600	-	I_{TM}=1000A, t_p=1000µs, di/dt=10A/µs, V_r=50V	µC
Q_{ra}	Recovered Charge, 50% chord	-	1100	1400		µC
I_{rm}	Reverse recovery current	-	120	-		A
t_{rr}	Reverse recovery time, 50% chord	-	18	-		µs
t_q	Turn-off time	-	200	-	I_{TM}=1000A, t_p=1000µs, di/dt=10A/µs, V_r=50V, V_{dr}=80%V_{DRM}, dV_{dr}/dt=20V/µs	µs
		-	300	-	I_{TM}=1000A, t_p=1000µs, di/dt=10A/µs, V_r=50V, V_{dr}=80%V_{DRM}, dV_{dr}/dt=200V/µs	
R_{thJK}	Thermal resistance, junction to heatsink	-	-	0.024	Double side cooled	K/W
		-	-	0.048	Single side cooled	K/W
F	Mounting force	19	-	26		kN
W_t	Weight	-	510	-		g

Notes: -
1) Unless otherwise indicated T_j=125°C.
2) For other clamp forces, please consult factory.

Notes on Ratings and Characteristics

1.0 Voltage Grade Table

Voltage Grade	V_{DRM} V_{DSM} V_{RRM} V	V_{RSM} V	V_D V_R DC V
06	600	700	420
07	700	800	490
08	800	900	560
09	900	1000	630
10	1000	1100	700

2.0 Extension of Voltage Grades

This report is applicable to other voltage grades when supply has been agreed by Sales/Production.

3.0 De-rating Factor

A blocking voltage de-rating factor of 0.13%/°C is applicable to this device for T_j below 25°C.

4.0 Repetitive dv/dt

Standard dv/dt is 1000V/µs.

5.0 Snubber Components

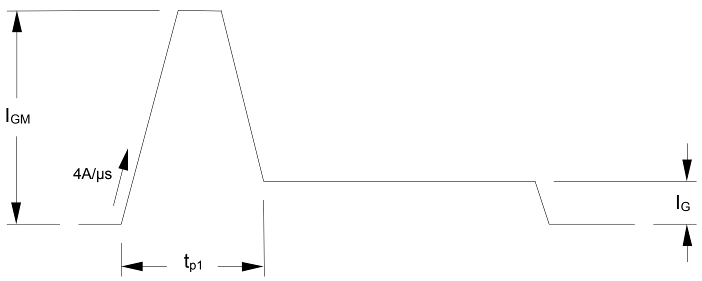
When selecting snubber components, care must be taken not to use excessively large values of snubber capacitor or excessively small values of snubber resistor. Such excessive component values may lead to device damage due to the large resultant values of snubber discharge current. If required, please consult the factory for assistance.

6.0 Rate of rise of on-state current

The maximum un-primed rate of rise of on-state current must not exceed 300A/µs at any time during turn-on on a non-repetitive basis. For repetitive performance, the on-state rate of rise of current must not exceed 150A/µs at any time during turn-on. Note that these values of rate of rise of current apply to the total device current including that from any local snubber network.

7.0 Gate Drive

The nominal requirement for a typical gate drive is illustrated below. An open circuit voltage of at least 30V is assumed. This gate drive must be applied when using the full di/dt capability of the device.



The magnitude of I_{GM} should be between five and ten times I_{GT}, which is shown on page 2. Its duration (t_{p1}) should be 20µs or sufficient to allow the anode current to reach ten times I_L, whichever is greater. Otherwise, an increase in pulse current could be needed to supply the necessary charge to trigger. The 'back-porch' current I_G should remain flowing for the same duration as the anode current and have a magnitude in the order of 1.5 times I_{GT}.

8.0 Computer Modelling Parameters

8.1 Device Dissipation Calculations

$$I_{AV} = \frac{-V_{T0} + \sqrt{V_{T0}^2 + 4 \cdot ff^2 \cdot r_T \cdot W_{AV}}}{2 \cdot ff^2 \cdot r_T}$$

and:

$$W_{AV} = \frac{\Delta T}{R_{th}}$$

$$\Delta T = T_{j\max} - T_K$$

Where V_{T0}=0.84V, r_T=0.108mΩ,

R_{th} = Supplementary thermal impedance, see table below and

ff = Form factor, see table below.

Supplementary Thermal Impedance							
Conduction Angle	30°	60°	90°	120°	180°	270°	d.c.
Square wave Double Side Cooled	0.0293	0.0285	0.0278	0.0271	0.0261	0.0249	0.024
Square wave Single Side Cooled	0.0534	0.053	0.0524	0.0518	0.0509	0.0497	0.048
Sine wave Double Side Cooled	0.0286	0.0276	0.0269	0.0263	0.0248		
Sine wave Single Side Cooled	0.0523	0.0517	0.0511	0.0497	0.0489		

Form Factors							
Conduction Angle	30°	60°	90°	120°	180°	270°	d.c.
Square wave	3.464	2.449	2	1.732	1.414	1.149	1
Sine wave	3.98	2.778	2.22	1.879	1.57		

8.2 Calculating V_T using ABCD Coefficients

The on-state characteristic I_T vs. V_T, on page 6 is represented in two ways;

(i) the well established V_{T0} and r_T tangent used for rating purposes and

(ii) a set of constants A, B, C, D, forming the coefficients of the representative equation for V_T in terms of I_T given below:

$$V_T = A + B \cdot \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

The constants, derived by curve fitting software, are given below for both hot and cold characteristics. The resulting values for V_T agree with the true device characteristic over a current range, which is limited to that plotted.

25°C Coefficients		125°C Coefficients	
A	0.746441	A	0.6821136
B	0.01352761	B	-6.744674×10^{-3}
C	4.783013×10^{-5}	C	4.313690×10^{-5}
D	4.302293×10^{-3}	D	7.540795×10^{-3}

8.3 D.C. Thermal Impedance Calculation

$$r_t = \sum_{p=1}^{p=n} r_p \cdot \left(1 - e^{\frac{-t}{\tau_p}}\right)$$

Where p = *1* to *n, n* is the number of terms in the series and:

- t = Duration of heating pulse in seconds.
- r_t = Thermal resistance at time t.
- r_p = Amplitude of p_{th} term.
- τ_p = Time Constant of r_{th} term.

The coefficients for this device are shown in the tables below:

D.C. Double Side Cooled					
Term	1	2	3	4	5
r_p	0.01249139	6.316833×10^{-3}	1.850855×10^{-3}	1.922045×10^{-3}	6.135330×10^{-4}
τ_p	0.8840810	0.1215195	0.03400152	6.742908×10^{-3}	1.326292×10^{-3}

D.C. Single Side Cooled						
Term	1	2	3	4	5	6
r_p	0.02919832	4.863568×10^{-3}	3.744798×10^{-3}	6.818034×10^{-3}	2.183558×10^{-3}	1.848294×10^{-3}
τ_p	6.298105	3.286174	0.5359179	0.1186897	0.02404574	3.379476×10^{-3}

9.0 Reverse recovery ratings

(i) Q_{ra} is based on 50% I_{rm} chord as shown in Fig. 1

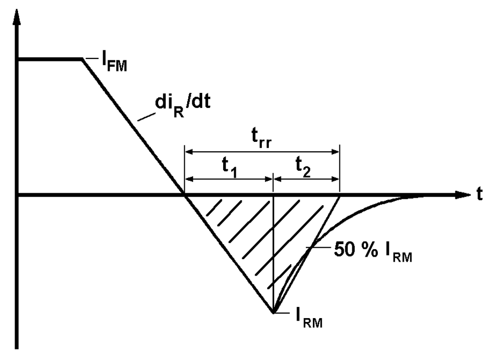


Fig. 1

(ii) Q_{rr} is based on a 150μs integration time i.e.

$$Q_{rr} = \int_0^{150\mu s} i_{rr}.dt$$

(iii)

$$K\ Factor = \frac{t_1}{t_2}$$

Curves

Figure 1 - On-state characteristics of Limit device

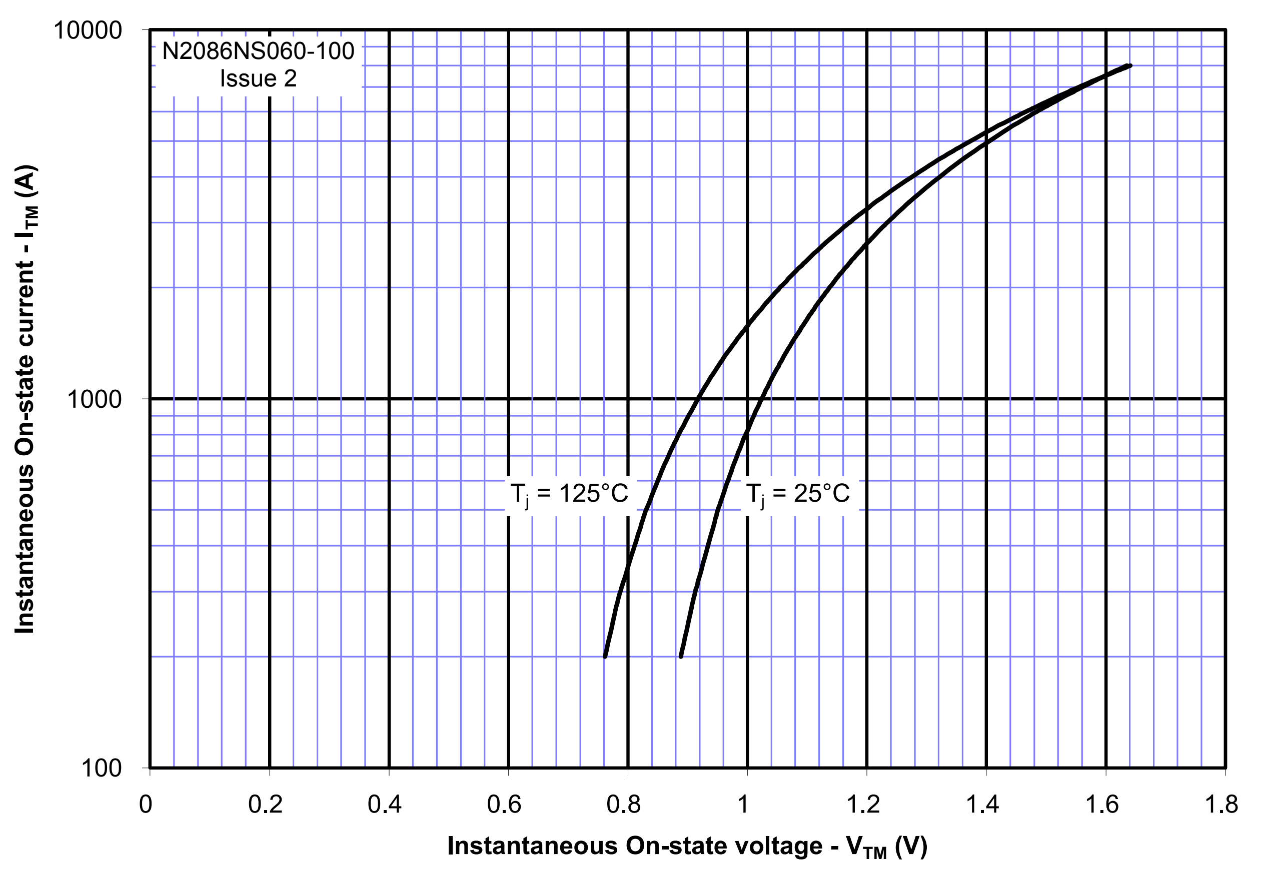


Figure 2 - Gate Characteristics - Trigger Limits

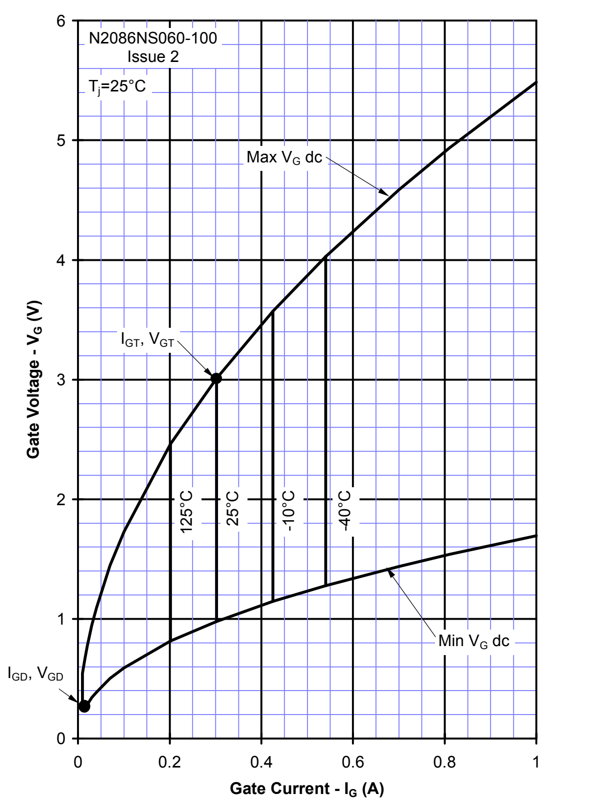


Figure 3 - Gate Characteristics - Power Curves

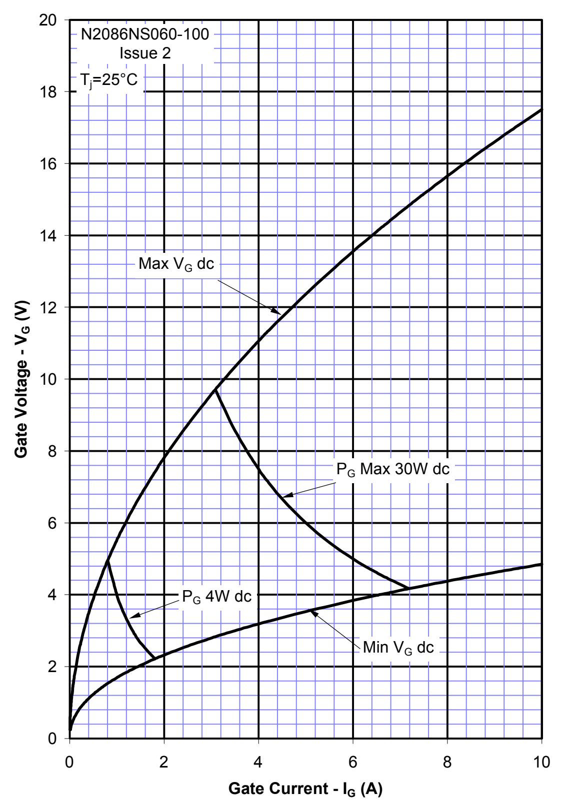


Figure 4 – Recovered Charge, Q_{rr}

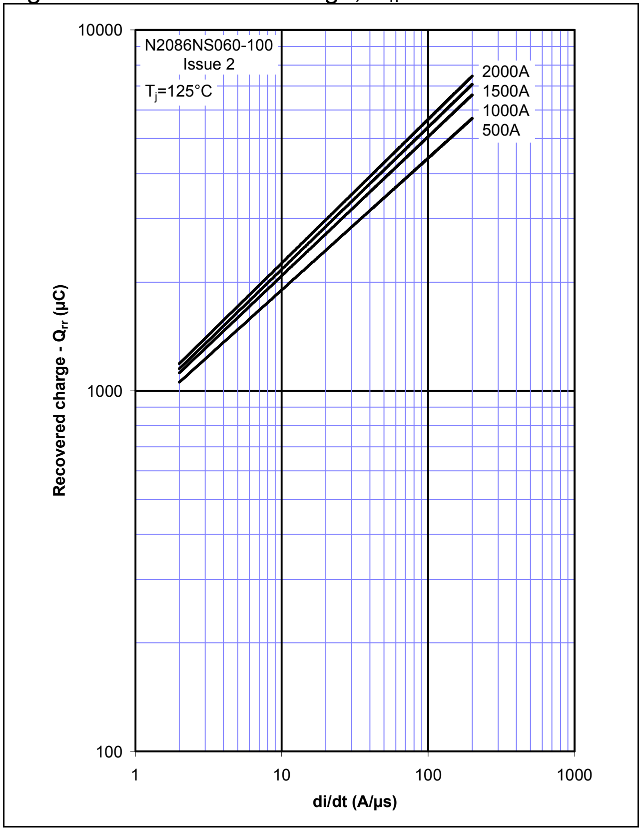


Figure 5 – Recovered charge, Q_{ra} (50% chord)

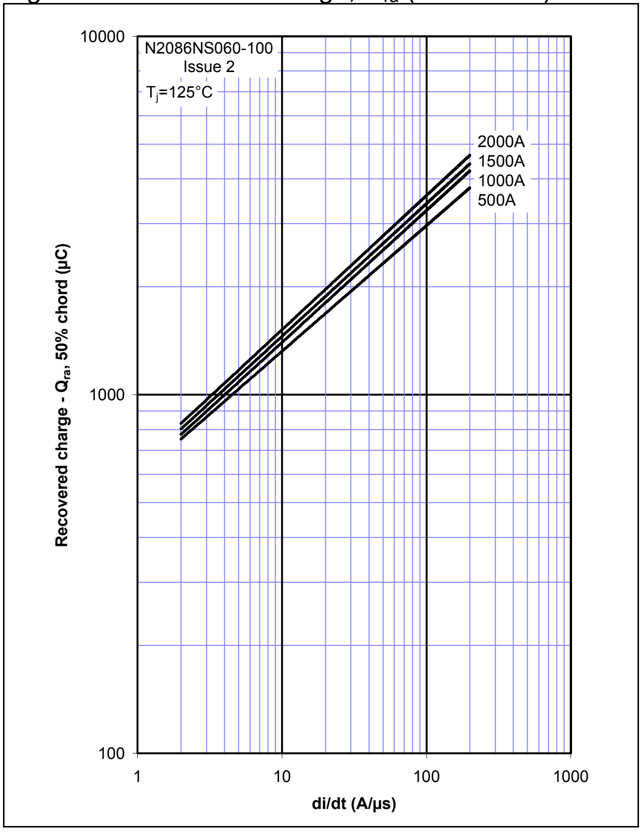


Figure 6 – Reverse recovery current, I_{rm}

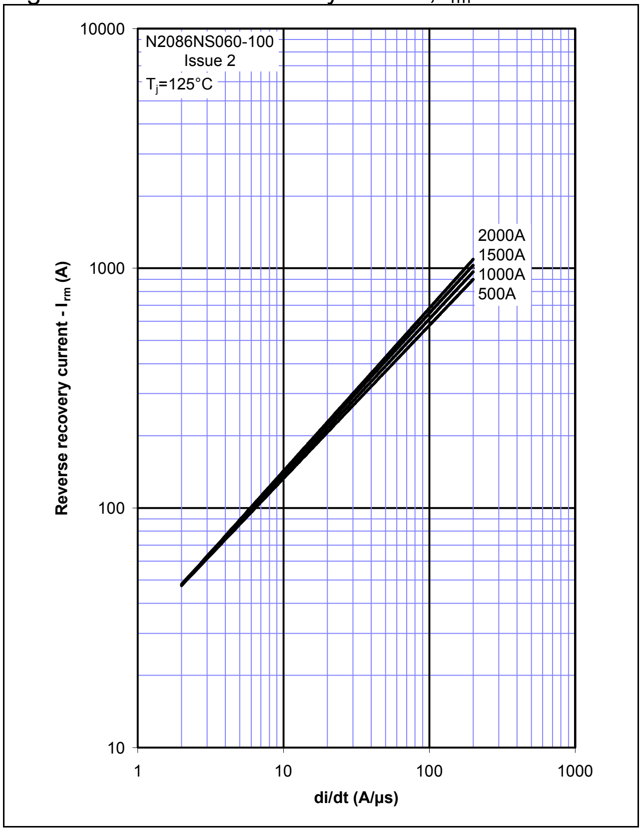


Figure 7 – Reverse recovery time, t_{rr} (50% chord)

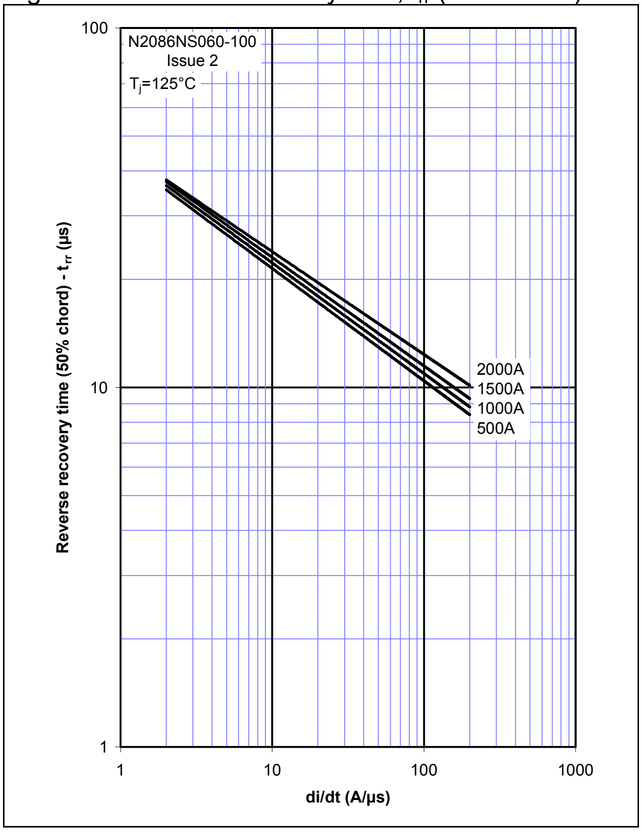


Figure 8 – On-state current vs. Power dissipation – Double Side Cooled (Sine wave)

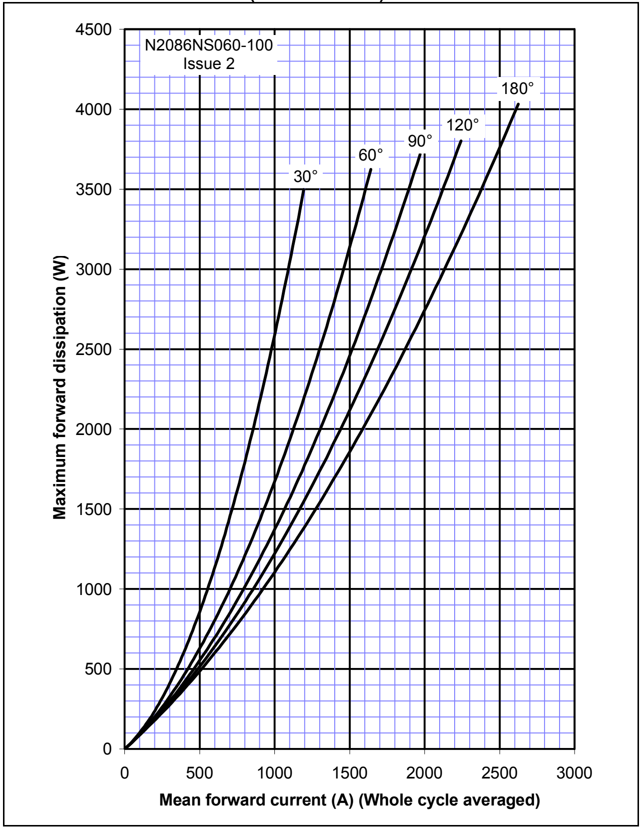


Figure 9 – On-state current vs. Heatsink temperature - Double Side Cooled (Sine wave)

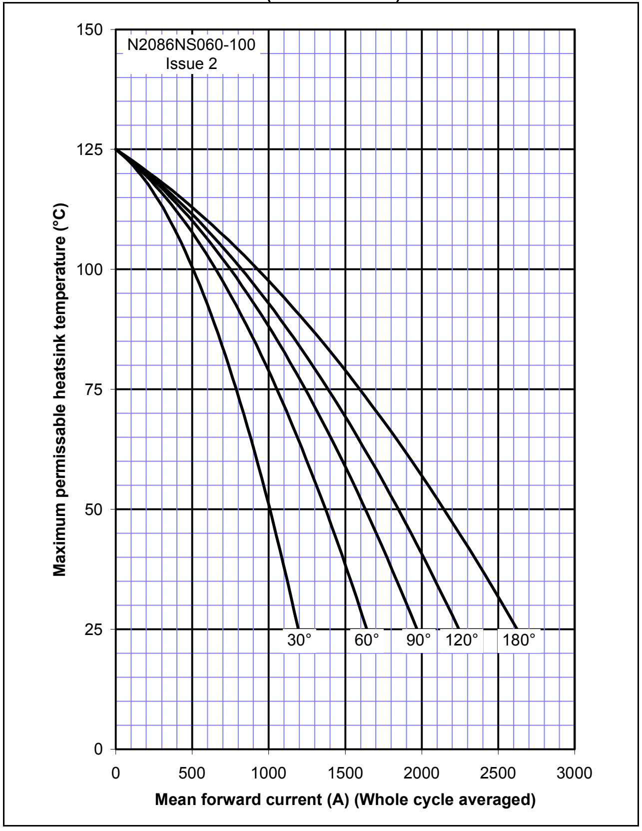


Figure 10 – On-state current vs. Power dissipation – Double Side Cooled (Square wave)

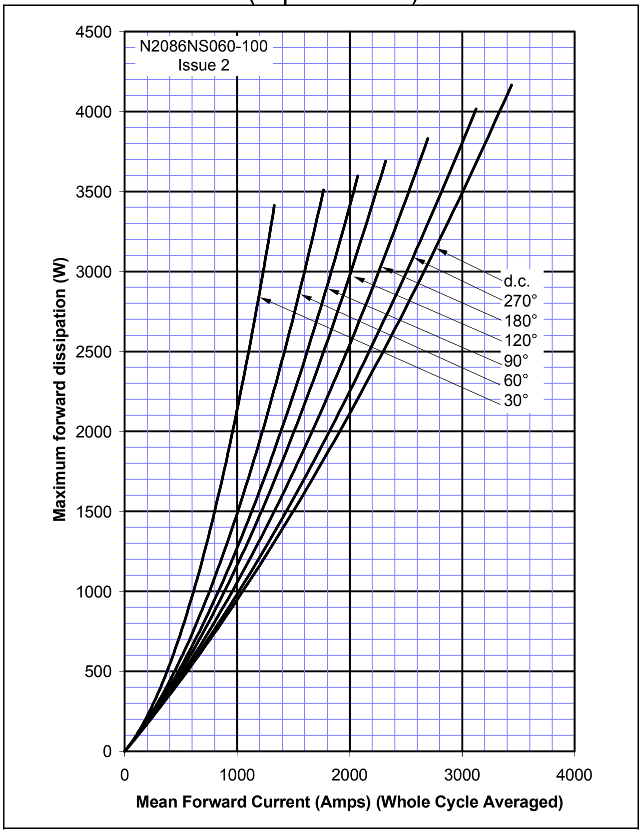


Figure 11 – On-state current vs. Heatsink temperature - Double Side Cooled (Square wave)

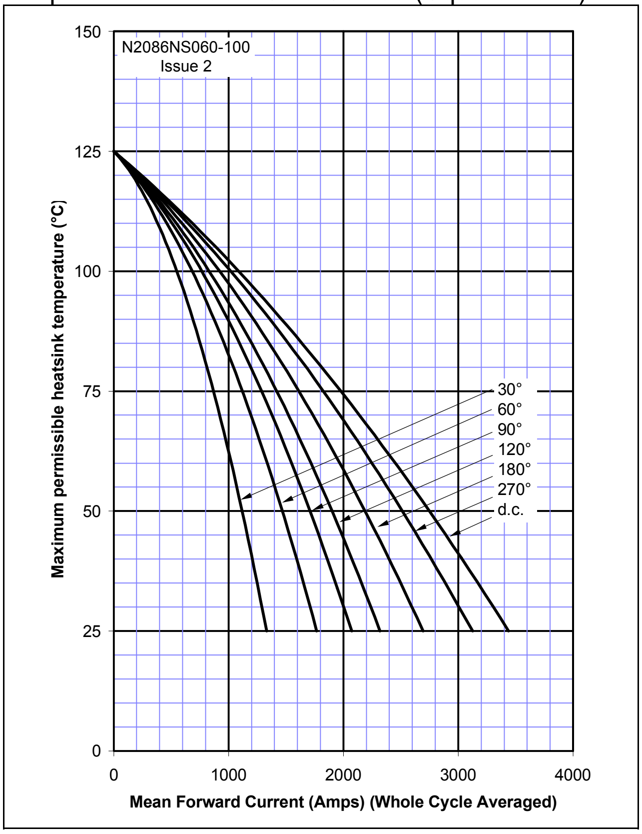


Figure 12 – On-state current vs. Power dissipation – Single Side Cooled (Sine wave)

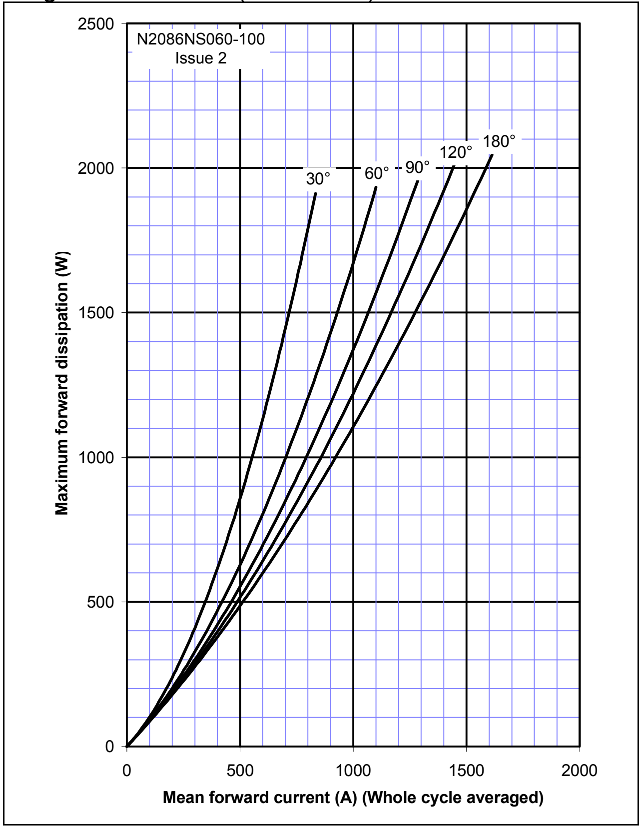


Figure 13 – On-state current vs. Heatsink temperature - Single Side Cooled (Sine wave)

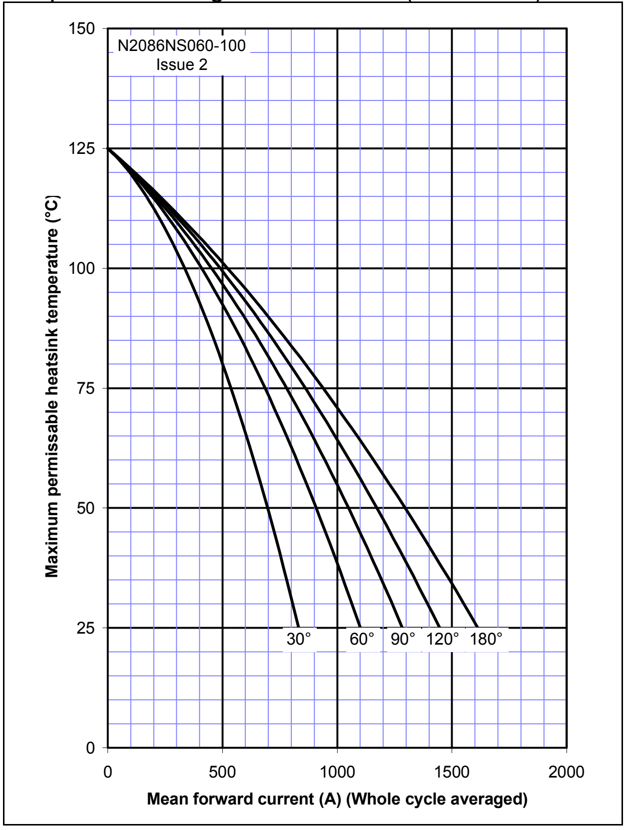


Figure 14 – On-state current vs. Power dissipation – Single Side Cooled (Square wave)

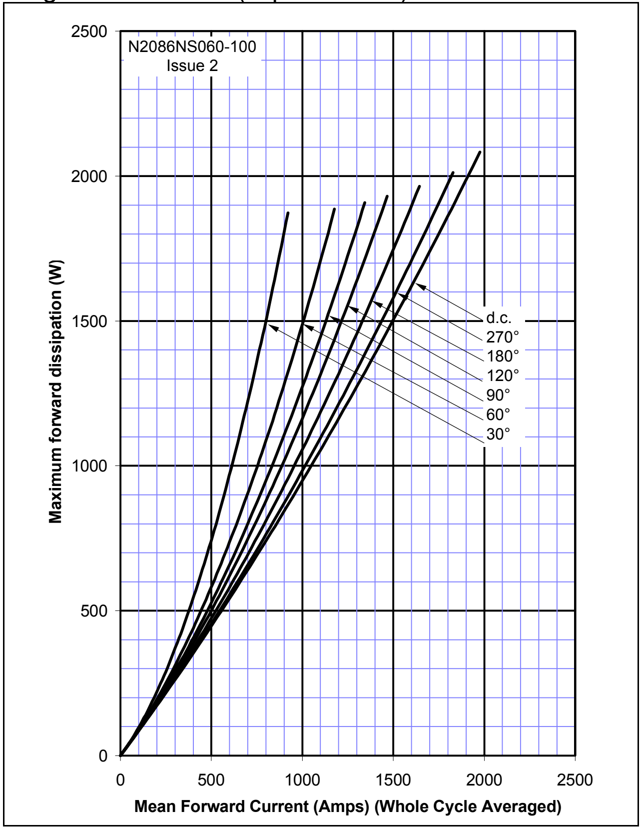


Figure 15 – On-state current vs. Heatsink temperature - Single Side Cooled (Square wave)

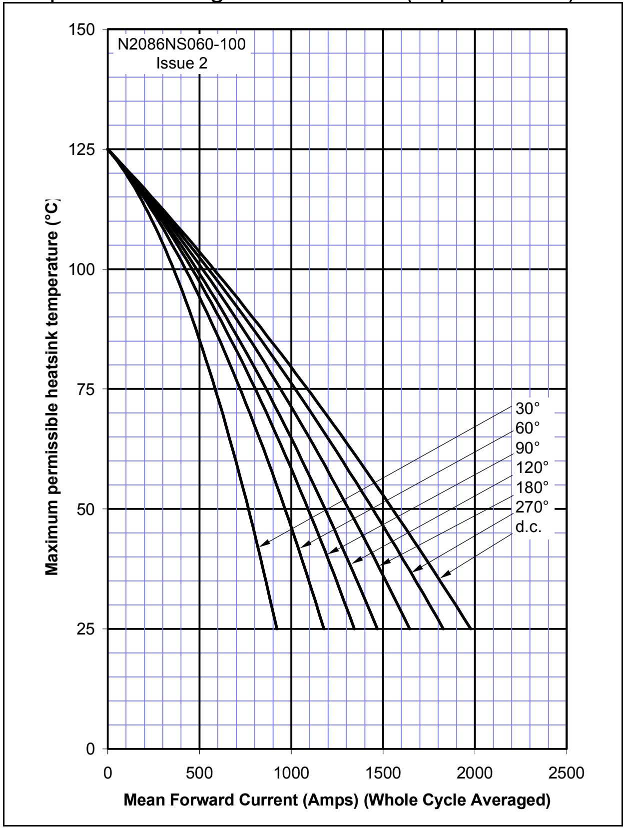


Figure 16 – Transient thermal impedance

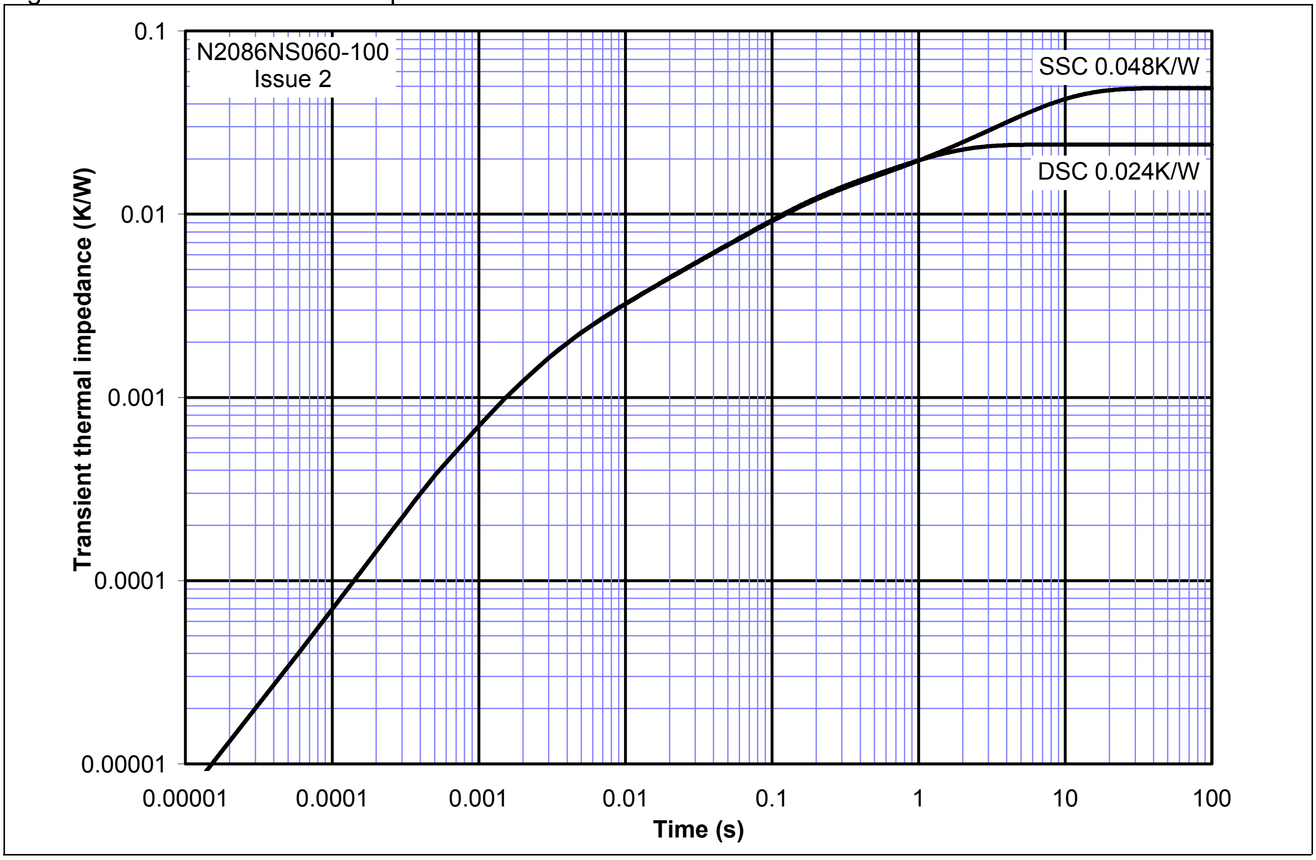
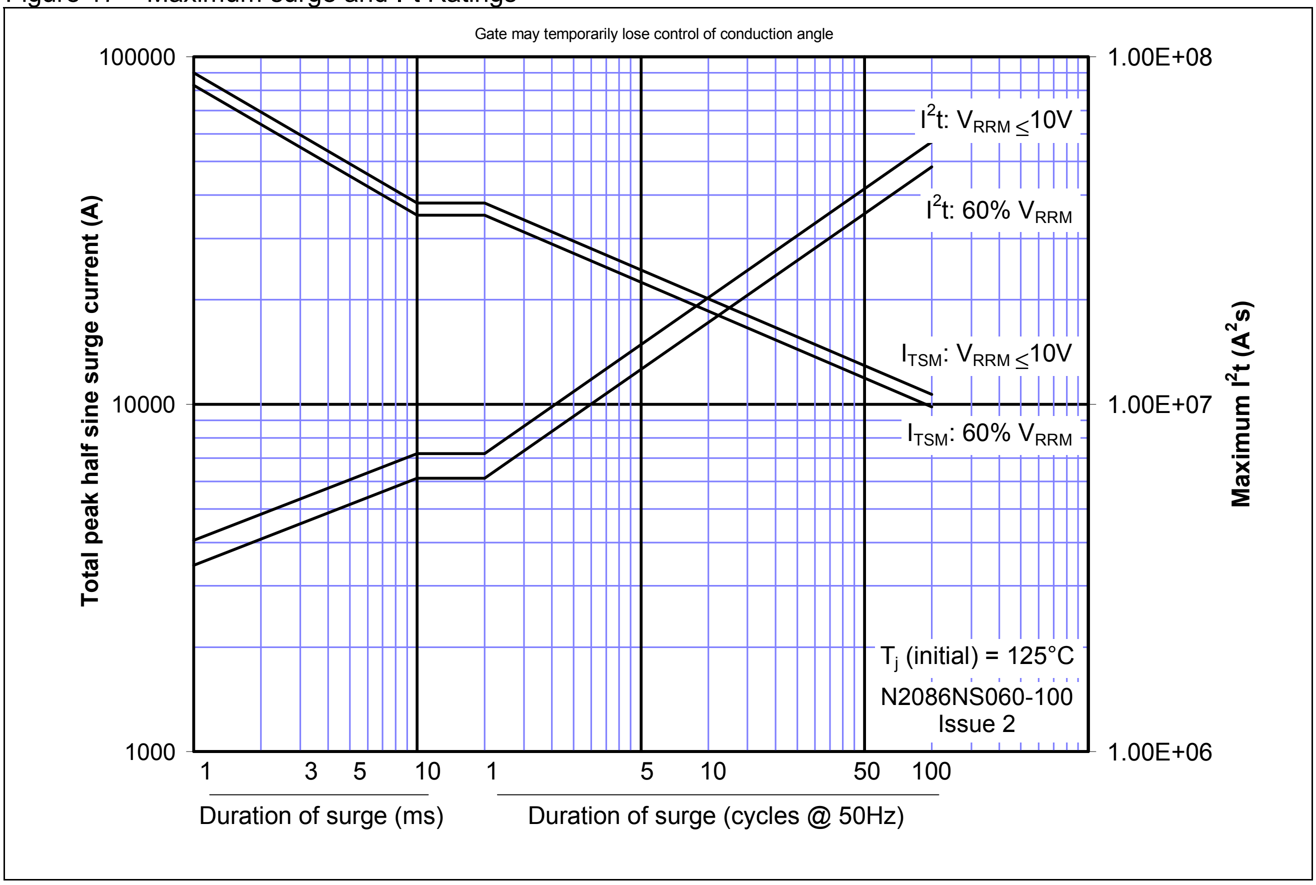
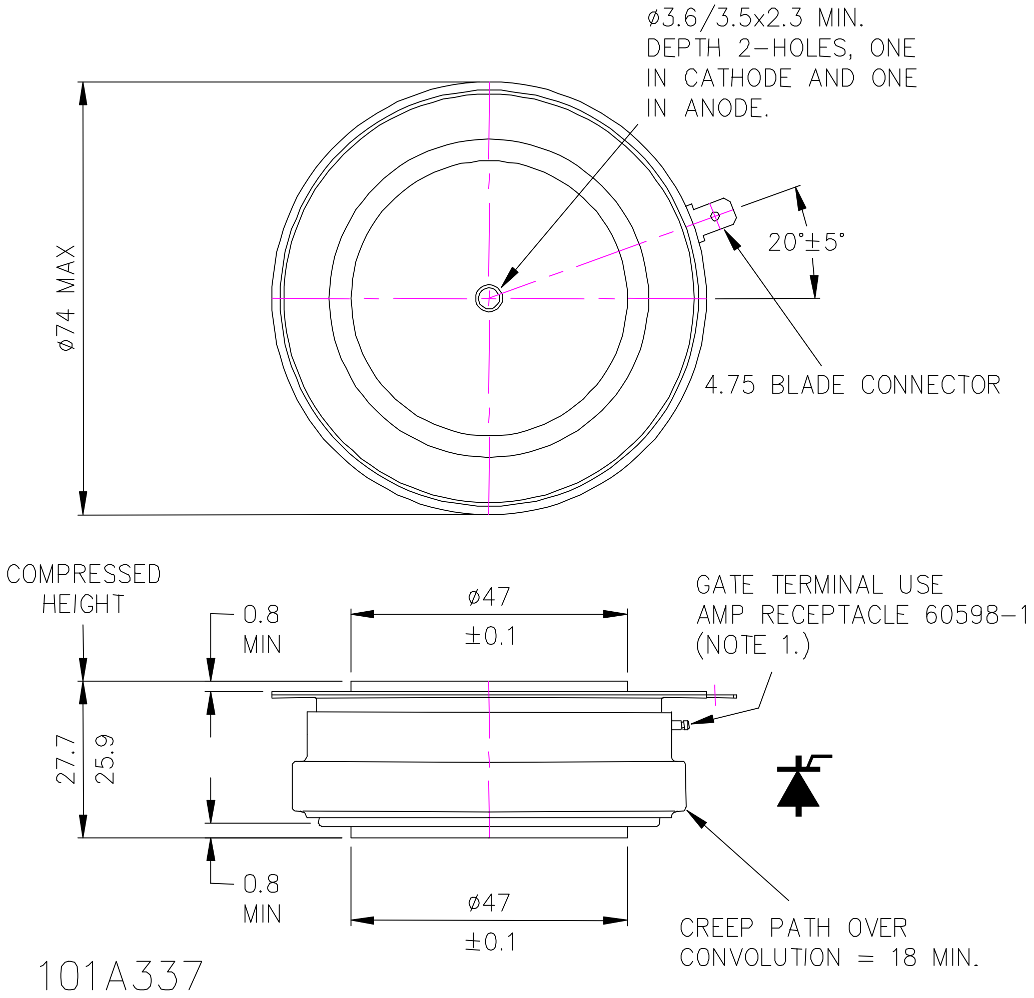


Figure 17 – Maximum surge and I^2t Ratings



Outline Drawing & Ordering Information



ORDERING INFORMATION		(Please quote 10 digit code as below)	
N2086	**NS**	**♦♦**	**0**
Fixed Type Code	Fixed outline code	Voltage code V_{DRM}/100 06-10	Fixed turn-off time code

Order code: N2086NS080 – 800V V_{DRM}, V_{RRM}, 26.1mm clamp height capsule.

IXYS Semiconductor GmbH
Edisonstraße 15
D-68623 Lampertheim
Tel: +49 6206 503-0
Fax: +49 6206 503-627
E-mail: marcom@ixys.de

WESTCODE
An IXYS Company

Westcode Semiconductors Ltd
Langley Park Way, Langley Park,
Chippenham, Wiltshire, SN15 1GE.
Tel: +44 (0)1249 444524
Fax: +44 (0)1249 659448
E-mail: WSL.sales@westcode.com

IXYS Corporation
3540 Bassett Street
Santa Clara CA 95054 USA
Tel: +1 (408) 982 0700
Fax: +1 (408) 496 0670
E-mail: sales@ixys.net

www.westcode.com

www.ixys.com

Westcode Semiconductors Inc
3270 Cherry Avenue
Long Beach CA 90807 USA
Tel: +1 (562) 595 6971
Fax: +1 (562) 595 8182
E-mail: WSI.sales@westcode.com